



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} max | I _D max T _A = +25°C |
|----------------------|------------------------------|--|
| 30V | 2.8Ω @ V _{GS} = 10V | 380mA |
| 307 | 3.8Ω @ $V_{GS} = 5V$ | 330mA |

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

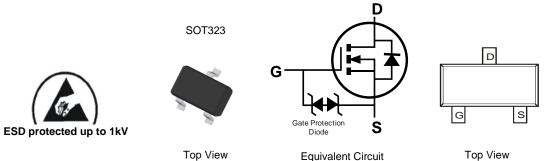
- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 1kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.006 grams (Approximate)



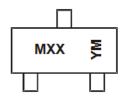
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|--------------|--------|-------------------|
| DMN63D8LW-7 | SOT323 | 3000/Tape & Reel |
| DMN63D8LW-13 | SOT323 | 10000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \text{MXX=} \underline{P} \text{roduct Type Marking Code} \\ \text{YM} = \overline{D} \text{ate Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: B} = 2014) \\ \text{M} = \text{Month (ex: 9} = \text{September)} \end{array}$

Date Code Key

| Bate Code It | | | | | | | | | | | | |
|--------------|------|------|------|------|------|------|------|------|------|------|------|------|
| Year | 2014 | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 |
| Code | В | С | D | Е | F | G | Н | I | J | K | L | M |
| | | | | | | | | | | | | |
| | | | | | | | | | l. | | | |
| Month | Jan | Feb | Mar | Apr | Мау | Jun | Jul | Aug | Sep | Oct | Nov | Dec |



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit | |
|---|----------------|------------------|------------------|------|---|
| Drain-Source Voltage | | V _{DSS} | 30 | V | |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Prain Correct (Nata C) V | I _D | 380 300 | mA | | |
| Continuous Drain Current (Note 6) V _{GS} = 10V | t<5s | I _D | 430 340 | mA | |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 19 | %) (Note 6) | I _{DM} | 1.2 | Α | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|--------------|----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | | P_{D} | 300 | mW |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{\theta JA}$ | 426 | °C/W |
| Total Power Dissipation (Note 6) | | P_{D} | 420 | mW |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\theta JA}$ | 301 | °C/W |
| Operating and Storage Temperature Range | | T _{J,} T _{STG} | -55 to +150 | °C |

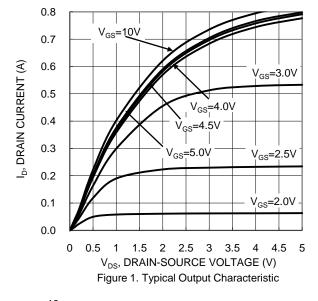
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

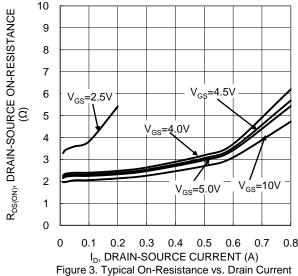
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|-----|------|-------|------|--|--|
| OFF CHARACTERISTICS (Note 7) | 1 | | 1 | 1 | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 30 | | — | V | V _{GS} = 0V, I _D = 250μA | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1.0 | μΑ | $V_{DS} = 30V$, $V_{GS} = 0V$ | |
| Gate-Source Leakage | I_{GSS} | _ | _ | ±10.0 | μΑ | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 8.0 | _ | 1.5 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | |
| | | | | 2.8 | | $V_{GS} = 10.0V, I_D = 250mA$ | |
| | | | _ | 3.8 | | $V_{GS} = 5.0V, I_D = 250mA$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | _ | 4.2 | Ω | $V_{GS} = 4.5V, I_D = 250mA$ | |
| | | | _ | 4.5 | | $V_{GS} = 4.0V, I_D = 250mA$ | |
| | | | _ | 13 | | $V_{GS} = 2.5V, I_D = 10mA$ | |
| Forward Transconductance | g FS | 80 | | _ | mS | V _{DS} = 10V, I _D = 0.115A | |
| Diode Forward Voltage | V _{SD} | | 8.0 | 1.2 | V | $V_{GS} = 0V, I_{S} = 115mA$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | C _{iss} | | 23.2 | _ | | | |
| Output Capacitance | Coss | | 3.0 | _ | pF | $V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$ | |
| Reverse Transfer Capacitance | C _{rss} | _ | 2.2 | _ | | | |
| Gate Resistance | R _G | | 79.9 | _ | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ | |
| Total Gate Charge V _{GS} = 10V | Qg | _ | 0.9 | _ | | | |
| Total Gate Charge V _{GS} = 4.5V | Qg | _ | 0.4 | _ | nC | $V_{GS} = 10V, V_{DS} = 30V,$ | |
| Gate-Source Charge | Q _{gs} | | 0.1 | _ | ПС | $I_D = 150 \text{mA}$ | |
| Gate-Drain Charge | Q _{gd} | _ | 0.2 | _ | | | |
| Turn-On Delay Time | t _{D(ON)} | | 2.3 | _ | | | |
| Turn-On Rise Time | t _R | _ | 3.9 | _ | ĺ | $V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V.$ | |
| Turn-Off Delay Time | t _{D(OFF)} | | 11.4 | _ | ns | $R_{GEN} = 25\Omega$ | |
| Turn-Off Fall Time | t _F | | 16.7 | _ | | | |

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

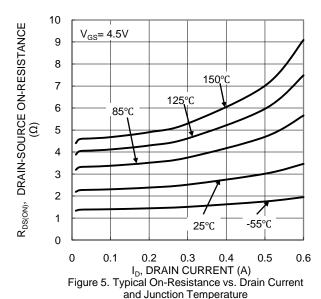
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

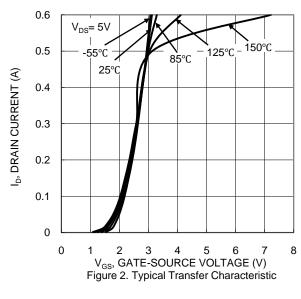


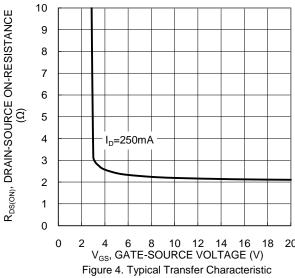




and Gate Voltage







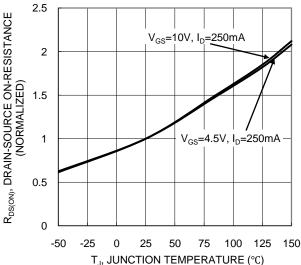


Figure 6. On-Resistance Variation with Junction
Temperature



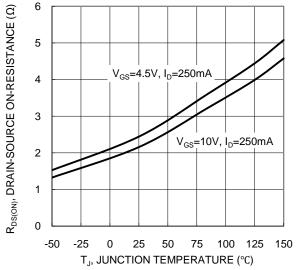
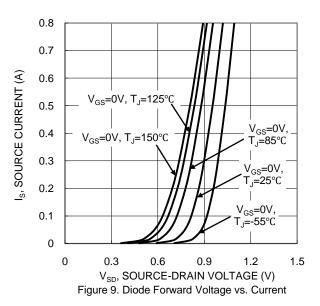
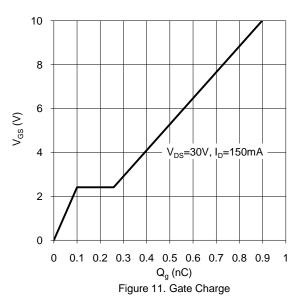
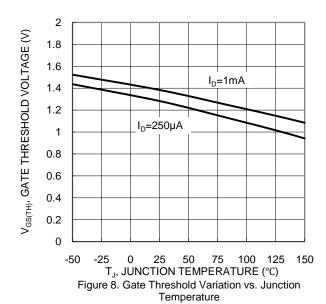
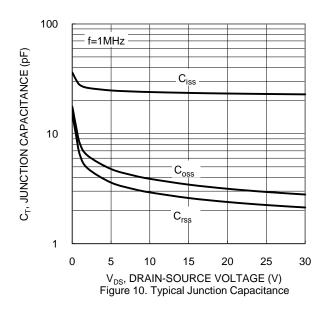


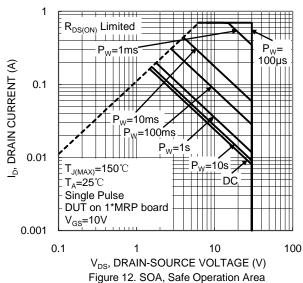
Figure 7. On-Resistance Variation with Junction Temperature













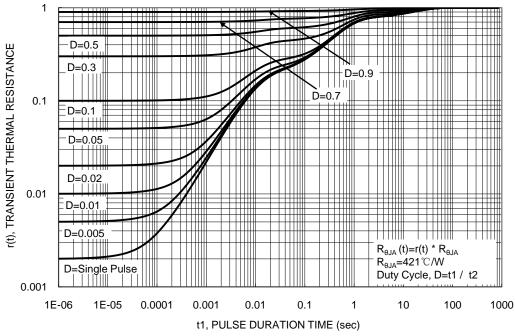
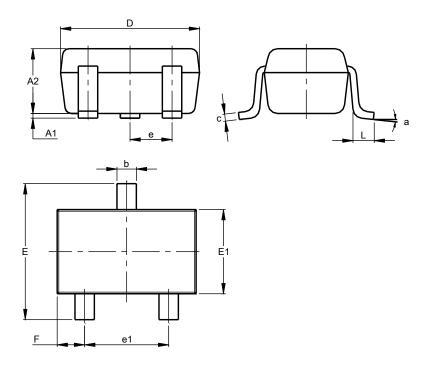


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

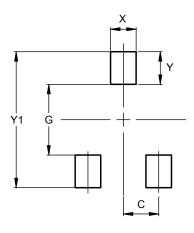


| SOT323 | | | | | | | | |
|--------|----------------------|---------|-------|--|--|--|--|--|
| Dim | Min | Max | Тур | | | | | |
| A1 | 0.00 | 0.10 | 0.05 | | | | | |
| A2 | 0.90 | 1.00 | 0.95 | | | | | |
| b | 0.25 | 0.40 | 0.30 | | | | | |
| С | 0.10 | 0.18 | 0.11 | | | | | |
| D | 1.80 | 2.20 | 2.15 | | | | | |
| Е | 2.00 | 2.20 | 2.10 | | | | | |
| E1 | 1.15 | 1.35 | 1.30 | | | | | |
| е | (|).650 E | SC | | | | | |
| e1 | 1.20 | 1.40 | 1.30 | | | | | |
| F | 0.375 | 0.475 | 0.425 | | | | | |
| L | 0.25 | 0.40 | 0.30 | | | | | |
| а | 8° | | | | | | | |
| All | All Dimensions in mm | | | | | | | |



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) | | |
|------------|------------------|--|--|
| С | 0.650 | | |
| G | 1.300 | | |
| Х | 0.470 | | |
| Y | 0.600 | | |
| Y1 | 2.500 | | |

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